

Electrostatic Discharged Protection Devices (ESD) Data Sheet

Description

Brightking's SDD32CXXL01 is designed to protect low voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, portable devices, digital cameras, power supplies and many other portable applications. It is designed to protect sensitive semiconductor components from damage or upset due to electrostatic discharge(ESD), electrical fast transients(EFT), and cable discharge events(CDE).

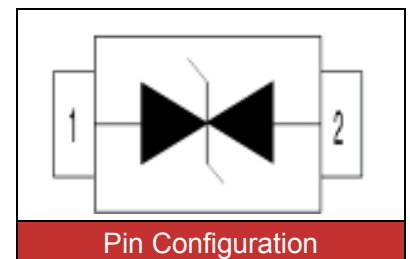


Contact : ±30kV
Air : ±30kV



Features

- IEC61000-4-2 ESD 30KV Air, 30KV contact compliance, ESD 25KV Air, 25KV contact compliance for SDD32C36L01
- SOD-323 surface mount package
- Protects bi-directional line
- Peak power dissipation of 320W under 8/20µs waveform
- Working voltage: 5V, 8V, 15V, 18V, 24V, 30V, 36V
- Low leakage current
- Low clamping voltage
- Solid-state silicon avalanche technology
- Lead Free/RoHS compliant
- Solder reflow temperature: Pure Tin-Sn, 260~270°C
- Flammability rating UL 94V-0
- Meets MSL level 1, per J-STD-020
- AEC-Q101 qualified



Applications

- | | |
|---|--|
| <ul style="list-style-type: none"> ● Cellular handsets & Accessories ● Cordless phones ● Personal digital assistants (PDAs) ● Notebooks & Handhelds | <ul style="list-style-type: none"> ● Portable instrumentation ● Digital cameras ● Peripherals |
|---|--|

Maximum Ratings

| Rating | Symbol | Value | Unit |
|---------------------------------------|-----------------------------------|----------|------|
| Peak pulse power (tp=8/20µs waveform) | P _{PP} | 320 | W |
| ESD voltage (Contact discharge) | V _{ESD} | ±30 | kV |
| ESD voltage (Air discharge) | | ±30 | |
| Storage & operating temperature range | T _{STG} , T _J | -55~+150 | °C |

Electrical Characteristics (T_J=25°C)
SDD32C05L01 (Marking: 2B)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|--------------------------------|------------------|----------------------|------|------|------|------|
| Reverse stand-off voltage | V _{RWM} | | | | 5 | V |
| Reverse breakdown voltage | V _{BR} | I _{BR} =1mA | 6 | | | V |
| Reverse leakage current | I _R | V _R =5V | | | 1 | μA |
| Clamping voltage (tp=8/20μs) | V _C | I _{PP} =1A | | | 9.8 | V |
| Clamping voltage (tp=8/20μs) | V _C | I _{PP} =10A | | 15 | | V |
| Off state junction capacitance | C _J | 0Vdc,f=1MHz | | 100 | | pF |

SDD32C08L01 (Marking: 2P)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|--------------------------------|------------------|----------------------|------|------|------|------|
| Reverse stand-off voltage | V _{RWM} | | | | 8 | V |
| Reverse breakdown voltage | V _{BR} | I _{BR} =1mA | 8.5 | | | V |
| Reverse leakage current | I _R | V _R =8V | | | 1 | μA |
| Clamping voltage (tp=8/20μs) | V _C | I _{PP} =1A | | 10 | | V |
| Clamping voltage (tp=8/20μs) | V _C | I _{PP} =10A | | | 20 | V |
| Off state junction capacitance | C _J | 0Vdc,f=1MHz | | 75 | | pF |

SDD32C15L01 (Marking: 2N)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|--------------------------------|------------------|----------------------|------|------|------|------|
| Reverse stand-off voltage | V _{RWM} | | | | 15 | V |
| Reverse breakdown voltage | V _{BR} | I _{BR} =1mA | 16.7 | | | V |
| Reverse leakage current | I _R | V _R =15V | | | 1 | μA |
| Clamping voltage (tp=8/20μs) | V _C | I _{PP} =8A | | 30 | | V |
| Off state junction capacitance | C _J | 0Vdc,f=1MHz | | 35 | | pF |

SDD32C18L01 (Marking: 2K)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|--------------------------------|------------------|----------------------|------|------|------|------|
| Reverse stand-off voltage | V _{RWM} | | | | 18 | V |
| Reverse breakdown voltage | V _{BR} | I _{BR} =1mA | 20 | | | V |
| Reverse leakage current | I _R | V _R =18V | | | 1 | μA |
| Clamping voltage (tp=8/20μs) | V _C | I _{PP} =1A | | | 29 | V |
| Clamping voltage (tp=8/20μs) | V _C | I _{PP} =5A | | | 40 | V |
| Off state junction capacitance | C _J | 0Vdc,f=1MHz | | 40 | | pF |

SDD32C24L01 (Marking: 2H)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|-------------------------------------|-----------|--------------|------|------|------|---------|
| Reverse stand-off voltage | V_{RWM} | | | | 24 | V |
| Reverse breakdown voltage | V_{BR} | $I_{BR}=1mA$ | 26.7 | | | V |
| Reverse leakage current | I_R | $V_R=24V$ | | | 1 | μA |
| Clamping voltage (tp=8/20 μs) | V_C | $I_{PP}=1A$ | | | 43 | V |
| Off state junction capacitance | C_J | 0Vdc,f=1MHz | | 37 | | pF |

SDD32C30L01-IP6 (Marking: 30C)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|-------------------------------------|-----------|--------------|------|------|------|---------|
| Reverse stand-off voltage | V_{RWM} | | | | 30 | V |
| Reverse breakdown voltage | V_{BR} | $I_{BR}=1mA$ | 32 | | | V |
| Reverse leakage current | I_R | $V_R=30V$ | | | 1 | μA |
| Clamping voltage (tp=8/20 μs) | V_C | $I_{PP}=1A$ | | 45 | | V |
| Clamping voltage (tp=8/20 μs) | V_C | $I_{PP}=6A$ | | 55 | | V |
| Off state junction capacitance | C_J | 0Vdc,f=1MHz | | 35 | | pF |

SDD32C36L01 (Marking: 36C)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|-------------------------------------|-----------|--------------|------|------|------|---------|
| Reverse stand-off voltage | V_{RWM} | | | | 36 | V |
| Reverse breakdown voltage | V_{BR} | $I_{BR}=1mA$ | 40 | | | V |
| Reverse leakage current | I_R | $V_R=36V$ | | | 1 | μA |
| Clamping voltage (tp=8/20 μs) | V_C | $I_{PP}=1A$ | | | 56 | V |
| Clamping voltage (tp=8/20 μs) | V_C | $I_{PP}=5A$ | | | 75 | V |
| Off state junction capacitance | C_J | 0Vdc,f=1MHz | | 30 | | pF |

Typical Characteristics Curves

Figure 1. Power Derating Curve

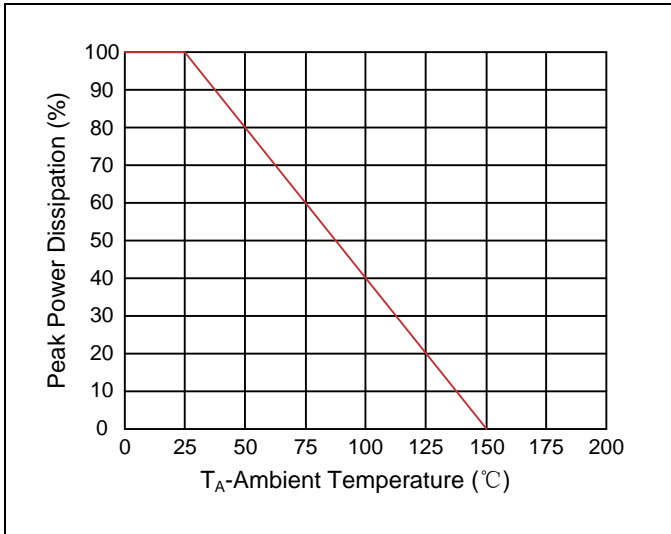


Figure 2. Pulse Waveform

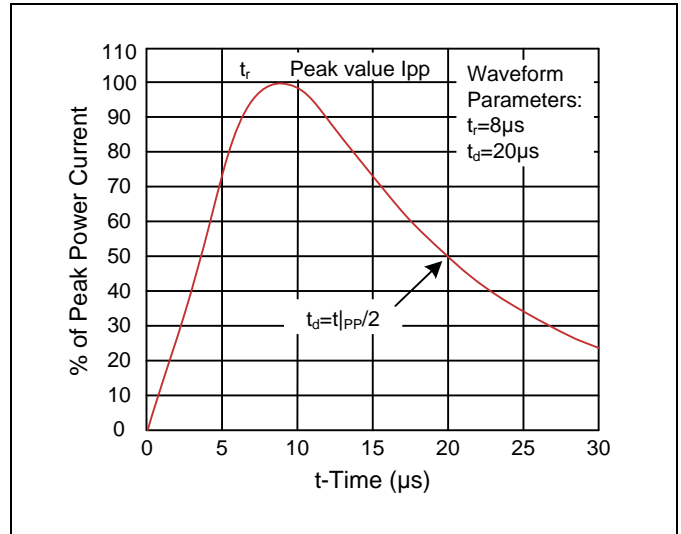
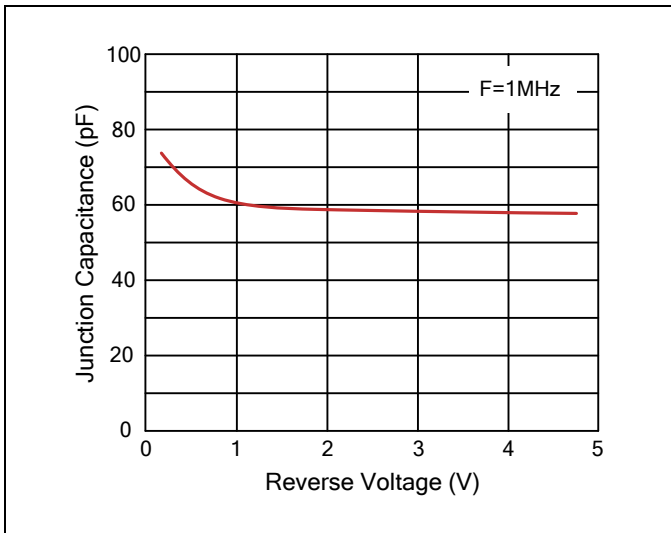
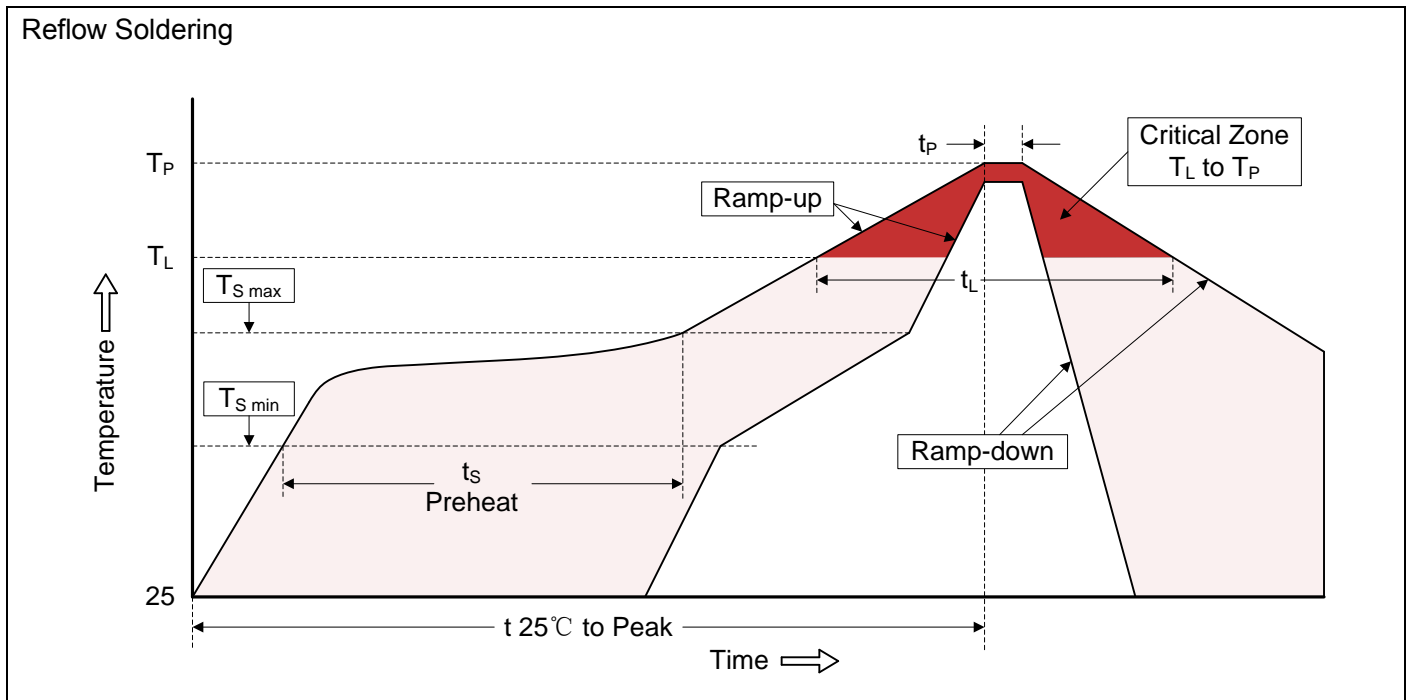


Figure 3. Capacitance vs. Reverse Voltage



Recommended Soldering Conditions



Recommended Condition

| Profile Feature | Pb-Free Assembly |
|---|----------------------------------|
| Average ramp-up rate (T_L to T_P) | 3°C/second max. |
| Preheat -Temperature Min ($T_{S\ min}$) -Temperature Max ($T_{S\ max}$) -Time (min to max) (t_s) | 150°C 200°C 60-180 seconds |
| $T_{S\ max}$ to T_L -Ramp-up Rate | 3°C/second max. |
| Time maintained above: -Temperature (T_L) -Time (t_L) | 217°C 60-150 seconds |
| Peak Temperature (T_P) | 260°C |
| Time within 5°C of actual Peak Temperature (t_P) | 20-40 seconds |
| Ramp-down Rate | 6°C/second max. |
| Time 25°C to Peak Temperature | 8 minutes max. |

Dimensions (SOD-323)

| | Dimension | | | | |
|---|-----------|-------------|-------|--------|-------|
| | Symbol | Millimeters | | Inches | |
| | | Min. | Max. | Min. | Max. |
| | A | 0.80 | 1.10 | 0.031 | 0.043 |
| B | - | 0.10 | - | 0.004 | |
| C | 0.20 | - | 0.008 | - | |
| D | 0.11 | 0.20 | 0.004 | 0.008 | |
| E | 1.15 | 1.35 | 0.045 | 0.053 | |
| F | - | 0.35 | - | 0.014 | |
| G | 1.60 | 1.80 | 0.063 | 0.071 | |
| H | 2.40 | 2.70 | 0.094 | 0.102 | |

Packaging

| <p>Tape</p> | Symbol | Dimension (mm) |
|--------------------|-------------------|----------------|
| | W | 8.00±0.30 |
| | P0 | 4.00±0.10 |
| | P1 | 4.00±0.10 |
| | P2 | 2.00±0.10 |
| | D0 | Φ1.55±0.10 |
| | D1 | Φ1.00±0.05 |
| | E | 1.75±0.10 |
| | F | 3.50±0.10 |
| | A | 1.48±0.10 |
| | A0 | 0.80±0.10 |
| | B | 3.00±0.10 |
| | B0 | 1.80±0.10 |
| | K | 1.05±0.10 |
| t | 0.25±0.05 | |
| <p>Reel</p> | D | Φ178.0±2.0 |
| | D2 | Φ13.0 |
| | W1 | 9.5 |
| | Quantity: 3000PCS | |

单击下面可查看定价，库存，交付和生命周期等信息

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